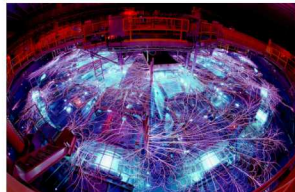


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Exceptional service in the national interest



SAND2019-10938C



Design of an Experimental Platform for In-Situ Single Quantum Emitter Detection

Michael Titze, Kulturansingh Hooghan, Han Htoon, Edward Bielejec

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Outline

Introduction

- Single Quantum Emitters & Quantum Computing
- Deterministic Placement of Single Quantum Emitters
- Prior Work

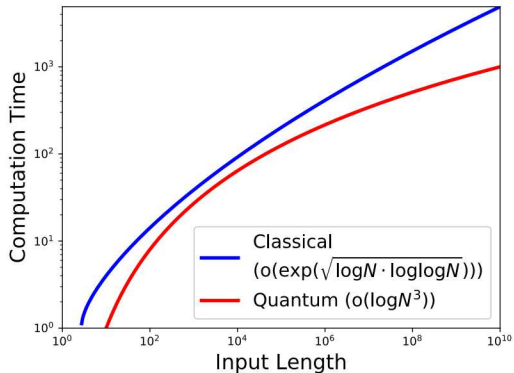
Experiment

- In-Situ Photoluminescence
- Instrument Design

Conclusion

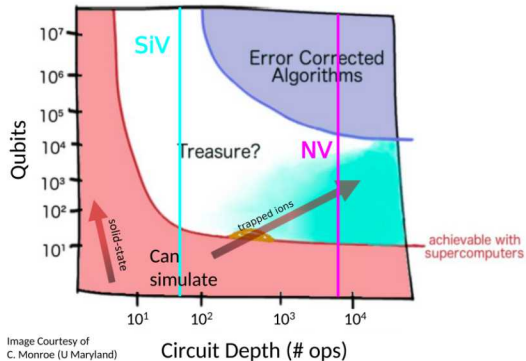
Advantages of Quantum Computing

- Potential for easily breaking current encryption
- Critical speedup of computationally hard problems



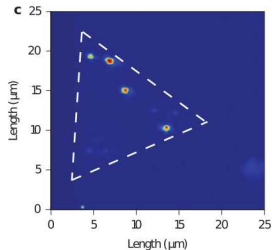
The (still current) Challenge of Quantum Computing

- Many qubits are needed, but at the same time long coherence times are required
- Solid state systems ideal candidate for high qubit density
 - Single color centers (defect or donor) in wide-bandgap materials: Potential for high-density and long coherence time



Deterministic Placement of Single-Quantum Emitters

- Coherent single photons are essential for transmitting quantum information
 - Single quantum emitters (SQE) are a source of coherent photons
- Currently SQE are mostly found, not made in samples
- To unlock the potential of SQE in solid state systems deterministic placement of SQE is necessary
 - Too close, interaction is too strong
 - Too far apart, hard to entangle



Y.M. He et al., Nature Nanotechnology 10, 497–502 (2015)

Focused ion beams allow precise (< 40 nm) implantation of defects in virtually any material and donors in materials such as diamond

-

T. Schröder et al., Nat. Comms., 8, 15376 (2017)

Focused Ion Beams from the nanoImplanter

- 100 kV accelerator using liquid metal alloy ion sources
- Access to ion species from approx. 1/3rd the periodic table



1 H																	2 He
3 Li	4 Be	Green: Demonstrated at SNL										5 B	6 C	7 N	8 O	9 F	10 Ne
Red: Attempting at SNL																	
Yellow: Demonstrated at other lab																	
11 Na	12 Mg											13 Al	14 Si	15 P	16 S	17 Cl	18 Ar
19 K	20 Ca	21 Sc	22 Ti	23 V	24 Cr	25 Mn	26 Fe	27 Co	28 Ni	29 Cu	30 Zn	31 Ga	32 Ge	33 As	34 Se	35 Br	36 Kr
37 Rb	38 Sr	39 Y	40 Zr	41 Nb	42 Mo	43 Tc	44 Ru	45 Rh	46 Pd	47 Ag	48 Cd	49 In	50 Sn	51 Sb	52 Te	53 I	54 Xe
55 Cs	56 Ba	* 57 La	72 Hf	73 Ta	74 W	75 Re	76 Os	77 Ir	78 Pt	79 Au	80 Hg	81 Tl	82 Pb	83 Bi	84 Po	85 At	86 Rn
87 Fr	88 Ra	* 89 Ac	* 104 Rf	105 Db	106 Sg	107 Bh	108 Hs	109 Mt	110 Ds	111 Rg	112 Cn	113 Nh	114 Fl	115 Mc	116 Lv	117 Ts	118 Og
			* 58 Ce	59 Pr	60 Nd	61 Pm	62 Sm	63 Eu	64 Gd	65 Tb	66 Dy	67 Ho	68 Er	69 Tm	70 Yb	71 Lu	
			* 90 Th	91 Pa	92 U	93 Np	94 Pu	95 Am	96 Cm	97 Bk	98 Cf	99 Es	100 Fm	101 Md	102 No	103 Lr	

Focused Ion Beams from the nanoImplanter

- Prior work has done timed and in-situ counted implantation but has not yet checked for in-situ SQE behaviour

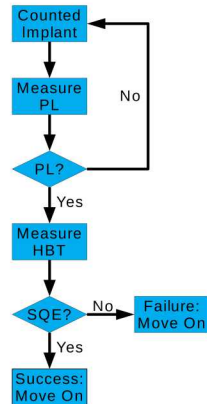


1 H																	2 He				
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37 Rb	38 Sr	39 Y	40 Zr	41 Nb	42 Mo	43 Tc	44 Ru	45 Rh	46 Pd	47 Ag	48 Cd	49 In	50 Sn	51 Sb	52 Te	53 I	54 Xe				
55 Cs	56 Ba	57 La	72 Hf	73 Ta	74 W	75 Re	76 Os	77 Ir	78 Pt	79 Au	80 Hg	81 Tl	82 Pb	83 Bi	84 Po	85 At	86 Rn				
87 Fr	88 Ra	89 Ac	104 Rf	105 Db	106 Sg	107 Bh	108 Hs	109 Mt	110 Ds	111 Rg	112 Cn	113 Nh	114 Fl	115 Mc	116 Lv	117 Ts	118 Og				
			58 Ce	59 Pr	60 Nd	61 Pm	62 Sm	63 Eu	64 Gd	65 Tb	66 Dy	67 Ho	68 Er	69 Tm	70 Yb	71 Lu					
			90 Th	91 Pa	92 U	93 Np	94 Pu	95 Am	96 Cm	97 Bk	98 Cf	99 Es	100 Fm	101 Md	102 No	103 Lr					

BUT: None of this tells us if we have a SQE or not until after the fact

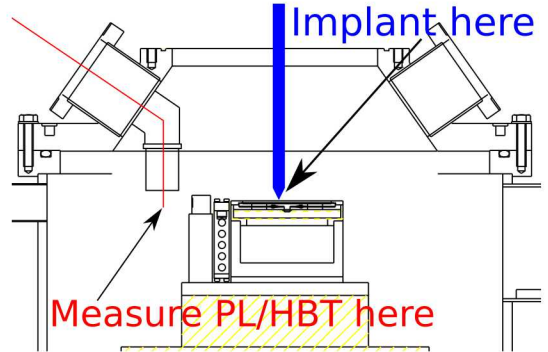
In-Situ Photoluminescence Detection for SQE Measurement

- Add a photoluminescence (PL) setup to the FIB column
- Use PL and Hanbury-Brown-Twiss (HBT) measurement to unambiguously determine SQE creation
- Implant, then check for PL immediately, if PL is visible, check for SQE with HBT
- Keep implanting until a SQE has been generated at the implant location, determined by HBT result



Design of the Custom In-Situ Microscope

- Microscope objective in vacuum chamber for in-situ PL detection
- z-axis movement to adjust for different focus of ion beam and optical microscope



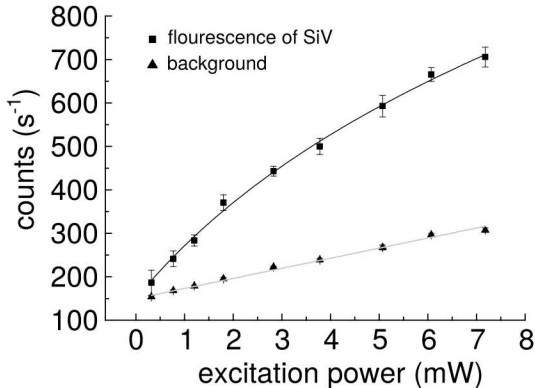
How Much Signal Can We Expect?

- Overall detection efficiency is estimated to be $\approx 10\%$

Component	Efficiency
BS Cube	45 %
Objective	80 %
NA	35 %
Dichroic	95 %

- To get $\geq 10^6$ cps, use ≥ 1 mW pump laser

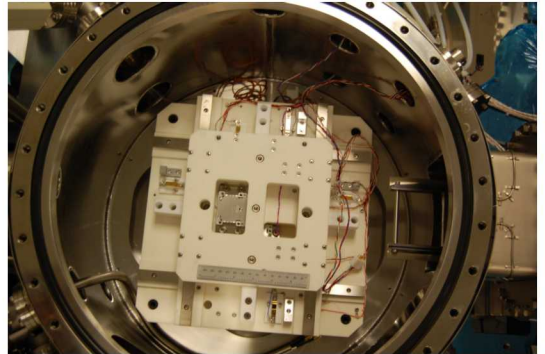
- Expected count rates from literature:
 $1 - 5 \times 10^5$ cps with 1 mW



Wang et al., J. Phys. B: At. Mol. Opt. Phys., 39, 1 (2006)

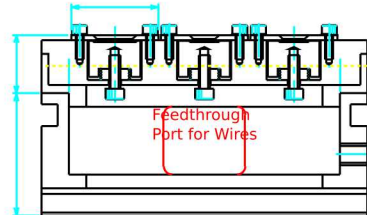
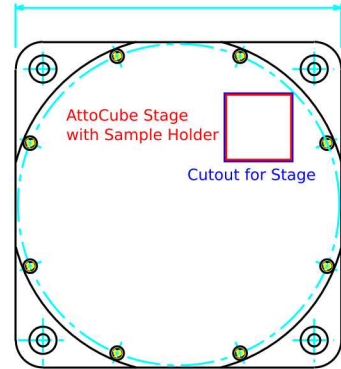
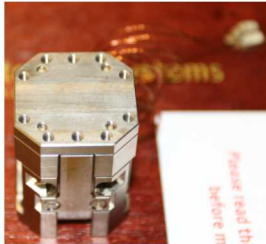
Sample Holder Redesign

- Current sample holder does not have z-adjust
- Need to adjust sample height to focus in FIB and microscope



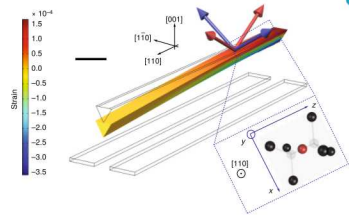
Sample Holder Redesign

- Current sample holder does not have z-adjust
- Need to adjust sample height to focus in FIB and microscope
- Add in capability to do counted implantation as well as in-situ PL

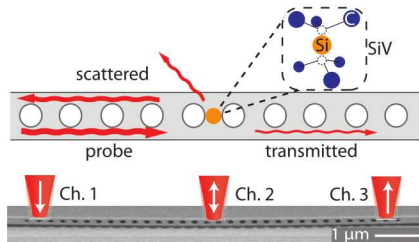


Conclusion

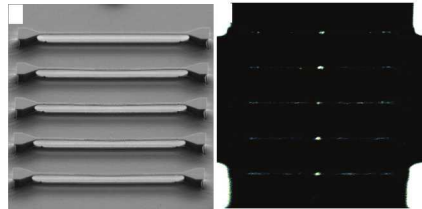
- Demonstrated the ability to perform high-resolution implantation (< 50 nm in x and y)
- Implantation depth accuracy (z axis) limited by straggles



Y.-I. Sohn et al., Nat. Commun. 9, 1212 (2018)



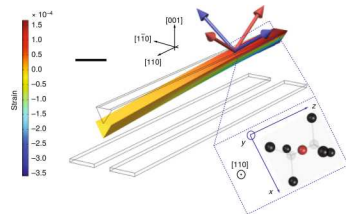
R. E. Evans et al., Science 362, 662–665 (2018)



A. Sipahigil et al., Science 354 (6314), 847–850 (2016)

Conclusion

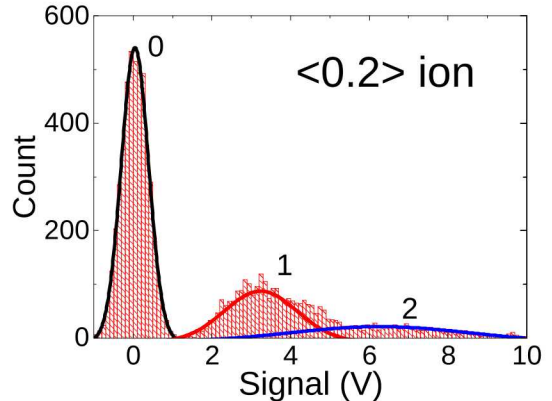
- Demonstrated the ability to perform high-resolution implantation (< 50 nm in x and y)
- Implantation depth accuracy (z axis) limited by straggle
- Currently silicon implantation into diamond is of limited use since the yield for optically active defect centers is low
 - Use the in-situ PL microscope on the nanolimplanter to deterministically create optically active defect centers with high resolution



Y.-I. Sohn et al., Nat. Commun. 9, 2012 (2018)

Counted Implantation

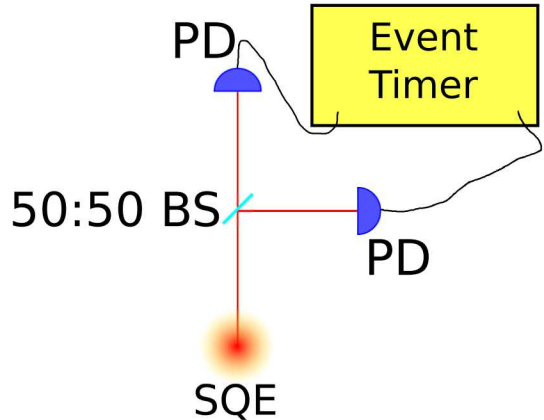
- Requires wire bondpads next to implantation region
- Does not confirm that implanted region is emitting light
- Problems arise with Si implantation into diamond where yield is only approx. 3%
 - Use SiC for testing of the microscope where yield is 10 – 20%, then move on to diamond



J. Abraham et al., Appl. Phys. Lett. 109, 063502 (2016)

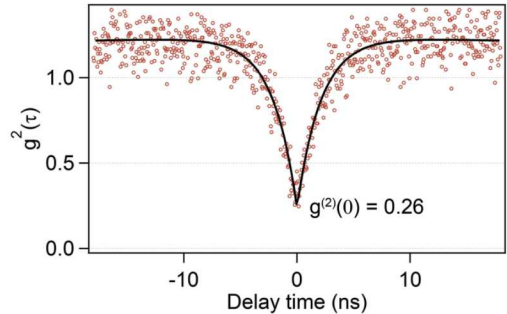
Hanbury-Brown-Twiss Measurement

- SQE can only emit one photon at a time
- Each photon will be transmitted or reflected at the beamsplitter being detected at only one of the two photodiodes



Hanbury-Brown-Twiss Measurement

- SQE can only emit one photon at a time
- Each photon will be transmitted or reflected at the beamsplitter being detected at only one of the two photodiodes
- Timed correlation measurement shows that within lifetime of SQE, correlation is close to zero



T. T. Tran et al., APL Photonics 2, 116103 (2017)